

Form PTO-1449 (Rev. 8-83)	U.S. Department of Commerce Patent and Trademark Office	Attorney Docket No. 0756-2218	Serial No. Not Yet Assigned
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Applicant: Hongyong ZHANG et al	
		Filing Date: October 25, 2000	Group: 2813

U.S. PATENT DOCUMENTS						
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
EP	4,657,775	04/14/1987	Shiori et al	-	-	
EP	5,654,203	11/23/1994	Ohtani et al	-	-	
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EP	5,488,000	01/30/1998	Zhang et al	-	-	

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	Document Number	Date	Country	Class	Subclass	Translation Yes No
EP	EP 0 174 553 A2	03/19/1986	Europe			
EP	61-070716	04/11/1986	Japan			Abstract
EP	6-029212	02/04/1994	Japan			Abstract
EP	2-140915	05/30/1990	Japan	437	40TFT	
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EP	5-90518	04/09/1993	Japan			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
EP	F. Spaepen et al., Crucial Issues in Semic. Mat. & Proc. Technol., S. Coffa et al., eds, Metal-enhanced Growth of Si ²
EP	J.E. Greene et al., Thin Solid Films 34 (1976) 27, "Metal Induced crystallization of R.F. sputtered a Si-films"
EP	ASM Handbook, Vol. 5, p510-531 (1994)
Examiner <i>Evan Pert</i>	Date Considered <i>5/21/01</i>

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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EP	J.R. Bosnell, et al., Thin Solid Films, 6(1970) 161 "...The Influence of Contact Materials or ... Crystallization..."
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EP	Y.N. Efokhin, et al., Appl. Phys. Lett., 63,23(1993) 3173 "... NiSi ₂ Formation ... on Preamorphized Silicon ..."
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EP	Y. Kawazu et al., Jpn. J. Appl. Phys., 29,12(1990)2698 "...Crystallization of A-Si:H Induced by Nickel..."
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EP	S. Wolfe & R.N. Tavber, "Silicon Processing got the VLSI Era" Vol I, 1986, P. 51-3, 335

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